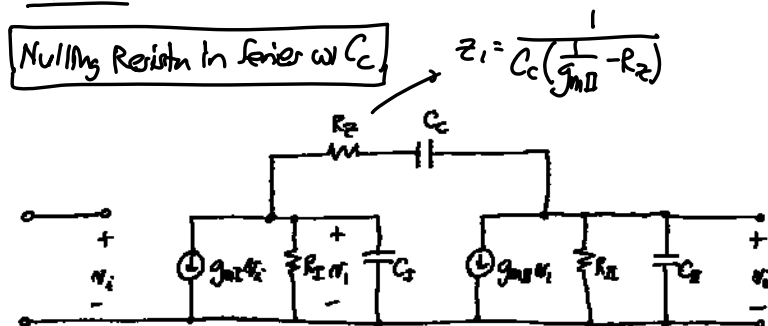


• Today:

- ⇒ RHP Zero Issues for Compensation (cont.)
- ⇒ Slew Rate II (design)
- ⇒ Settling Time

Last Time -



Zero Placement Strategies

- ① Eliminate $z_1 \rightarrow$ move it to ∞ .
 - ② Eliminate p_3 by placing z_1 on top of it.
 - ③ Eliminate p_2 by placing z_1 on top of it.
- ↳ most attractive... but...

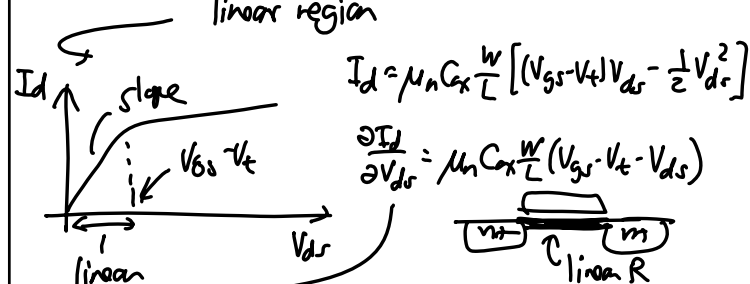
Remark. If settling time is important, then approach ③ may not be the best approach. The reason is that if the zero is not exactly equal to the pole, the a "doublet" ensues, which actually can hurt the settling time.

Discussed in a handout to be posted on the course website. → also, discussed in Razavi, problem 10.19.

Actual Implementation

⇒ resistors are too big! → ∴ implement using a much smaller MOS resistor!

MOS Resistor: just an MOS transistor operated in the linear region

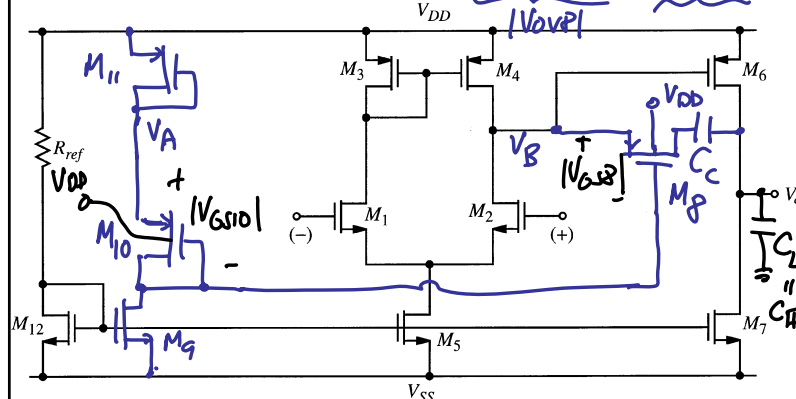


$$R_{s,r} = \left[\frac{dI_d}{dV_{ds}} \right]^{-1} \bigg|_{V_{gs}=V_{GS}, V_{ds}=V_{DS}} = \frac{1}{\mu_n C_{ox} \frac{W}{L} (V_{GS} - V_t - V_{DS})} \approx \frac{1}{g_{ds}}$$

a variable resistor controlled by V_{GS} !

Actual Implementation

$V_{DS} = 0V \Rightarrow R_p = \frac{1}{\mu_p C_{ox} (W/L)_p (|V_{GS}| - |V_{t,p}|)}$ Replicate This



Design:

Need $V_A = V_B \rightarrow |V_{GS1}| = |V_{GS6}|$, know that $|V_{t1}| = |V_{t6}|$

$$\sqrt{\frac{2I_{D11}}{\mu_p C_{ox}(\frac{W}{L})_1}} = \sqrt{\frac{2I_{D6}}{\mu_p C_{ox}(\frac{W}{L})_6}}$$

$$\left(\frac{W}{L}\right)_1 = \left(\frac{W}{L}\right)_6 \frac{I_{D11}}{I_{D6}} = \left(\frac{W}{L}\right)_6 \frac{I_{D10}}{I_{D6}}$$

Also need $|V_{GS10}| = |V_{GS9}|$

Because $V_A = V_B \rightarrow V_{S10} = V_{S9} \rightarrow |V_{t10}| = |V_{t9}|$

$$\therefore |V_{GS10}| = |V_{GS9}| = \sqrt{\frac{2I_{D10}}{\mu_p C_{ox}(\frac{W}{L})_9}}$$

Then:

$$R_8 = \frac{1}{\mu_p C_{ox}(\frac{W}{L})_8 \sqrt{\frac{2I_{D10}}{\mu_p C_{ox}(\frac{W}{L})_9}}} = \frac{\sqrt{\mu_p C_{ox}(WL)_{10}}}{\mu_p C_{ox}(\frac{W}{L})_8 \sqrt{2I_{D10}}}$$

Case: Eliminate p_2 by placing z_1 on top of it.

$$R_2 = \frac{C_c + C_L}{g_{m6} C_c} = \frac{\sqrt{\mu_p C_{ox}(WL)_{10}}}{\mu_p C_{ox}(\frac{W}{L})_6 \sqrt{2I_{D10}}}$$

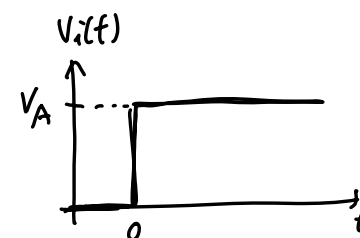
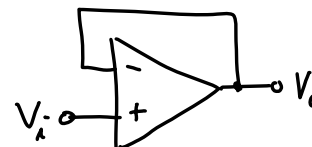
$$\sqrt{2\mu_p C_{ox}(WL)_6 I_{D6}}$$

$$\left(\frac{W}{L}\right)_8 = \left(\frac{W}{L}\right)_6 \left(\frac{W}{L}\right)_{10} \frac{I_{D6}}{I_{D10}} \cdot \left(\frac{C_c}{C_c + C_L}\right)$$

Case: Make $z_1 \rightarrow \infty$.

$$R_2 = \frac{1}{g_{m6}} \Rightarrow \left(\frac{W}{L}\right)_8 = \left(\frac{W}{L}\right)_6 \left(\frac{W}{L}\right)_{10} \frac{I_{D6}}{I_{D10}}$$

Slew Rate (from before)



Using Laplace Xform Theory:

$$\frac{V_o}{V_i}(s) = \frac{1}{1 + \frac{s}{\omega_1}} = \frac{1}{1 + s\tau_1}$$

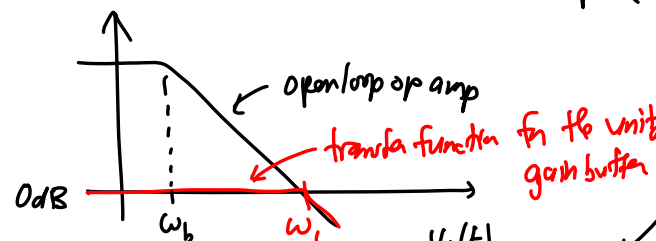
\sim single (dominant) pole

$$V_i(s) = \frac{V_A}{s}$$

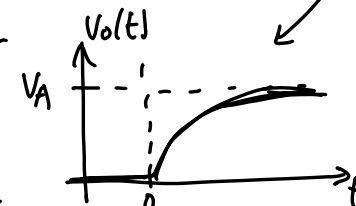
$$V_o(s) = \frac{V_A}{s(1 + s\tau_1)} = \frac{V_A}{s} - \frac{V_A}{s + \frac{1}{\tau_1}}$$

\Downarrow Inverse Laplace Xform

$$V_o(t) = V_A(1 - e^{-t/\tau_1}) \leftarrow \text{expected response}$$

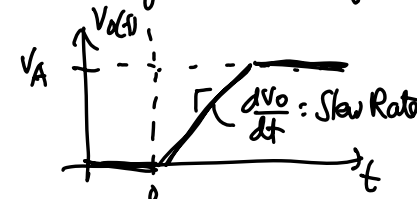


Expectation

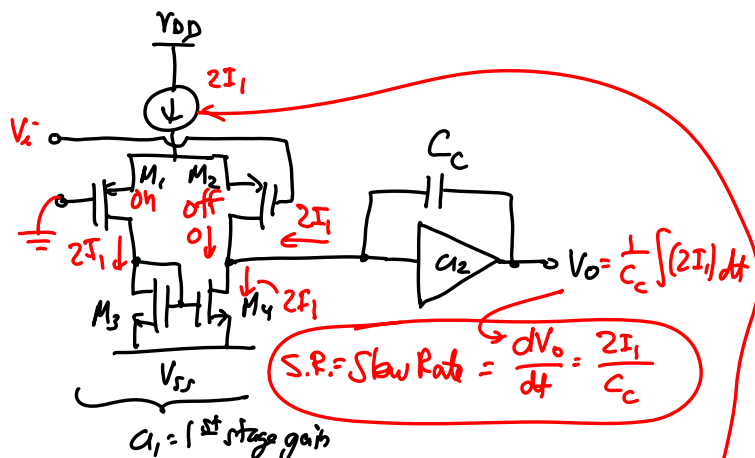


Actually:

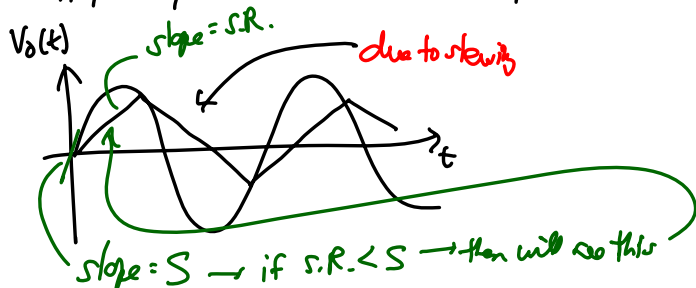
Why this slow rise?



Reason: 1st or 2nd stage of op amp cannot source enough current to mimic the slope (or speed) of a fast rising input signal.



If apply a very fast (i.e., high freq., large amplitude) sinusoid:



Terms of design variables:

$$S.R. = \frac{dV_o}{dt} = \frac{I_{xcm}}{C_c} \uparrow \quad \boxed{\frac{I_{xcm}}{G_{m1}} \omega_{ul} A_o = S.R.}$$

$$C_c = \frac{G_{m1}}{\omega_{ul} A_o} \leftarrow \text{closed loop gain}$$

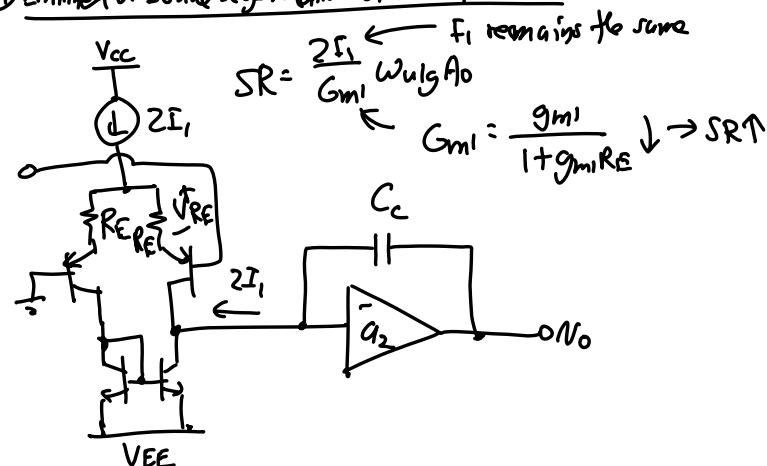
$$\omega_{ul} = \omega @ |T(j\omega)| = 1$$

To Increase S.R.:

- ① Decrease G_{m1} ← transconductance of 1st stage
- ② Increase ω_{ul} → increase ω_2
 ↳ limited by the Xstrin freq. range
- ③ Use a larger A_o , if possible.
 closed loop gain (only if permitted by the application)

Increasing S.R. via G_m Reduction

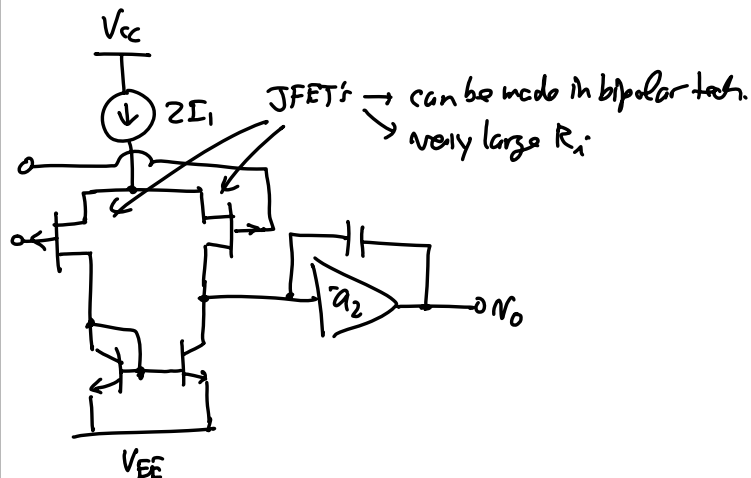
① Emitter or Source Degeneration of the Input Stage—



Limitations.

- ① R_E mismatch → V_{os}
 ↳ must limit V_{RE} to limit V_{os}
- ② $R_E \uparrow \rightarrow \text{gain} \downarrow$ (SR-gain trade-off)
- ③ R_E contributes thermal noise → must limit to preserve the noise performance of the op amp.

② FET Input Device -



For FETs: $\frac{g_m}{I_D} \approx \frac{2}{V_{GS} - V_t} \leftarrow \sim 0.2V$

For BJTs: $\frac{g_m}{I_C} = \frac{1}{V_T} \leftarrow 26mV$

$\frac{\text{FET S.R.}}{\text{BJT S.R.}} = \frac{\frac{I_D}{g_{mF}} \omega_{uF}}{\frac{I_C}{g_{mB}} \omega_{uB}} = \frac{\frac{V_{GS} - V_t}{2}}{V_T} = \frac{V_{GS} - V_t}{2 V_T} = \frac{260}{26} \approx 10$

Limitations.

- ① Higher V_{OS} .
- ② Increased voltage noise.
(But decreased current noise.)

Settling Time

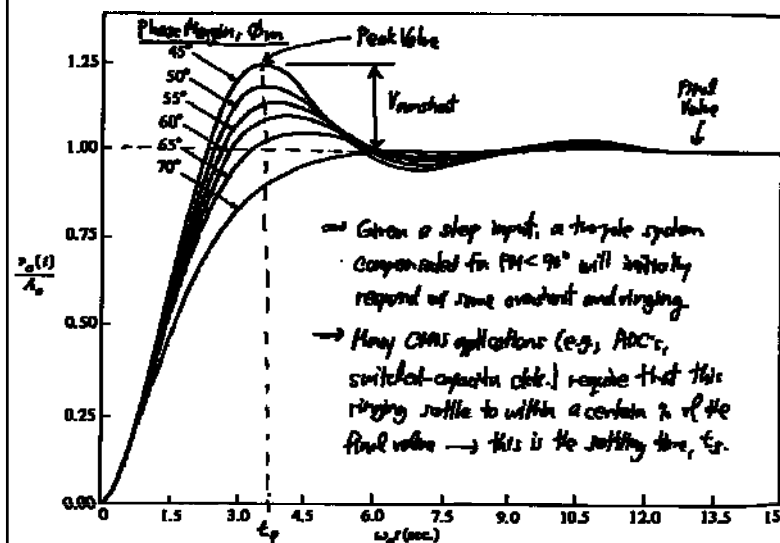
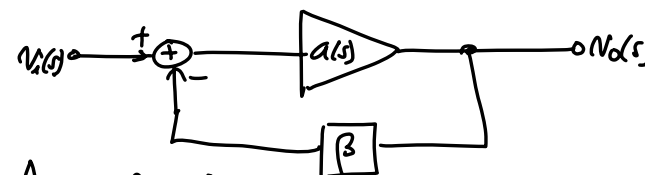


Figure 8.2-3 Response of second-order system with various phase margins.

Obtain Expressions for:

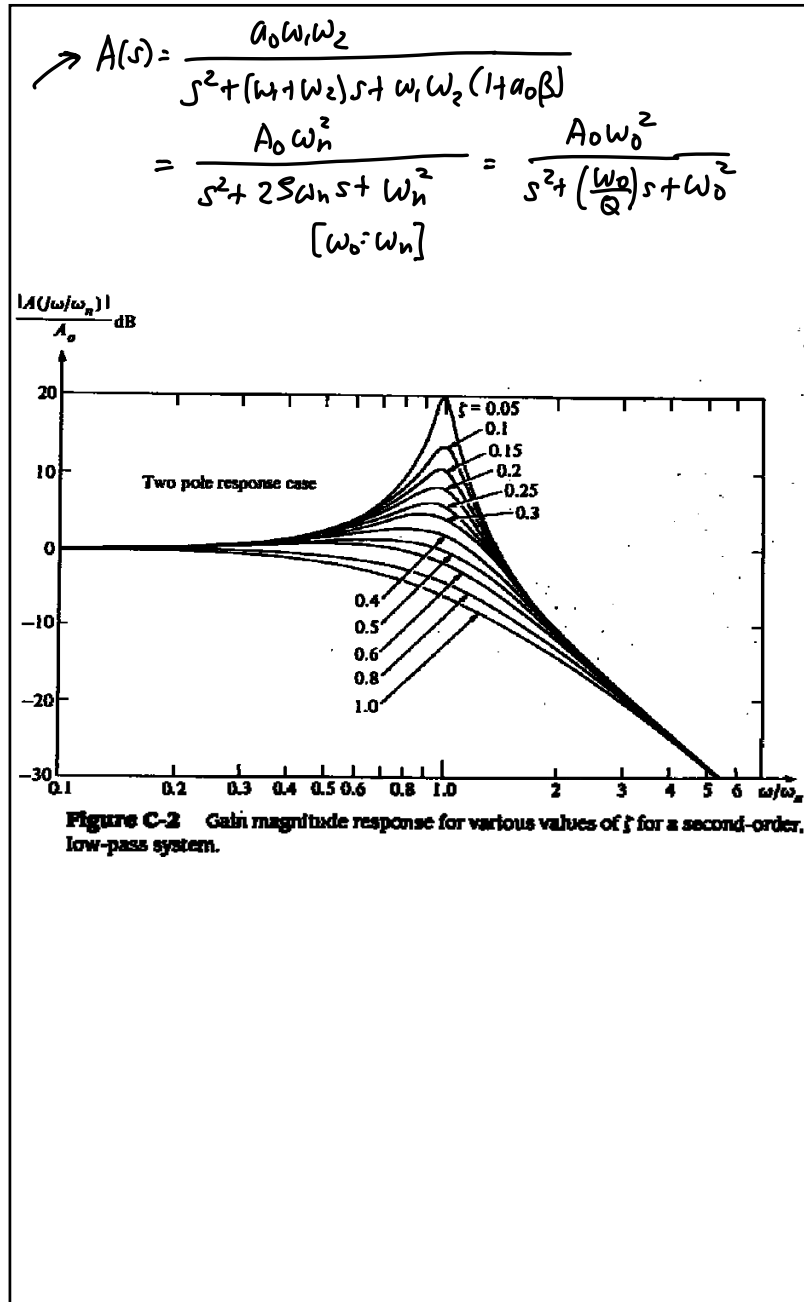
- ① $V_{overshoot}$
 - ② Settling Time, T_s
- as functions of phase margin, Φ_m



Assume: $\beta = \text{const w/ freq.}$

$A(s) = \frac{V_O(s)}{V_i(s)} = \frac{a(s)}{1 + a(s)\beta}$

$a(s) = \frac{a_0}{(1 + \frac{s}{\omega_1})(1 + \frac{s}{\omega_2})} = \frac{a_0 \omega_1 \omega_2}{(s + \omega_1)(s + \omega_2)}$



Asymmetrical Slew Rate

Very often the SR is not symmetrical in some FB ckt.

⇒ SR can be different for (+)only and (-)only going output signals

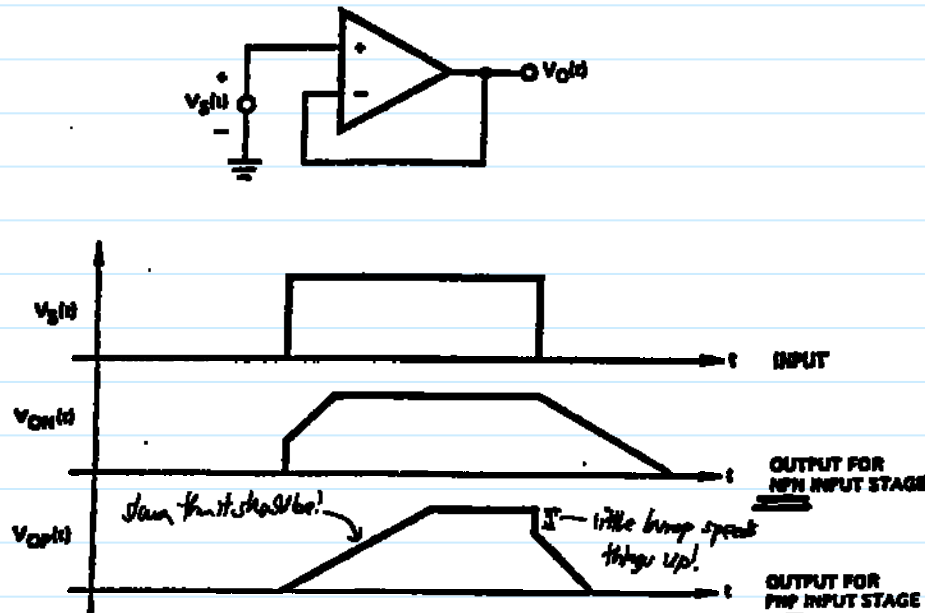
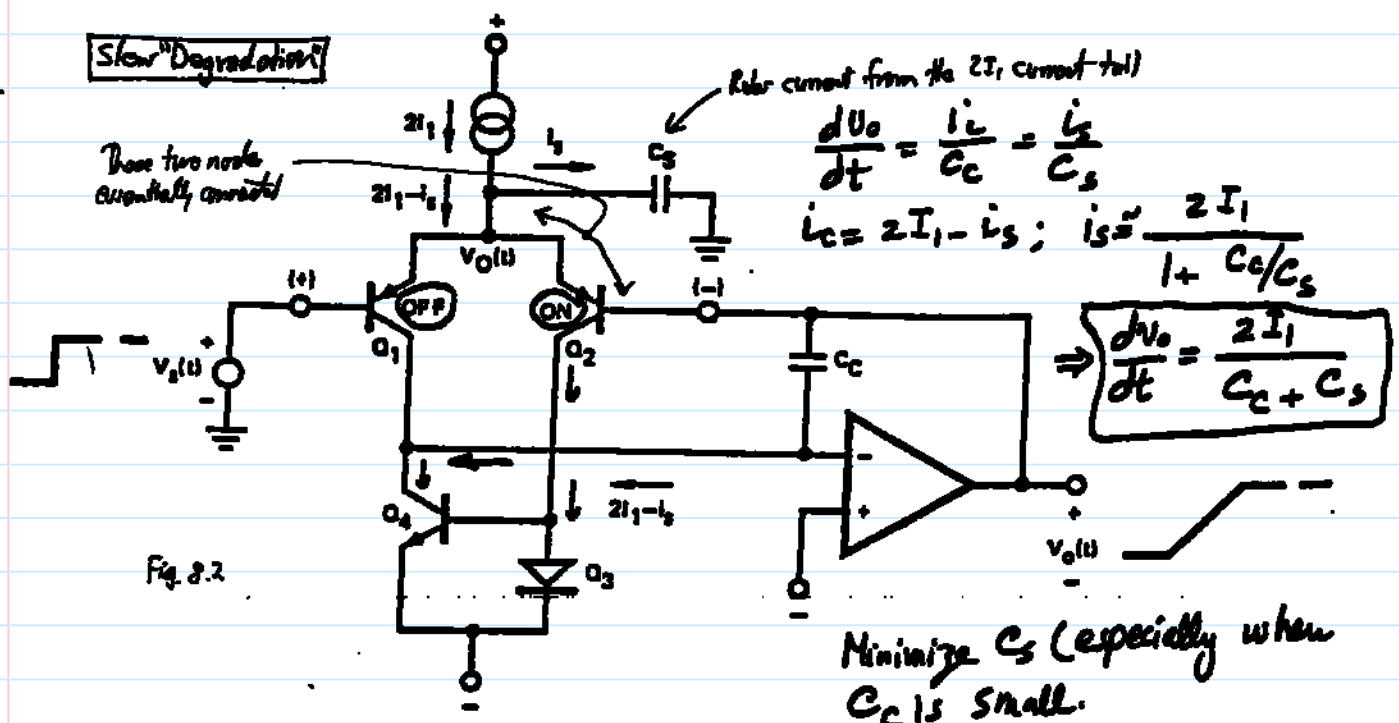


Fig. 8.1

Fig. 16. Large signal response of the voltage follower. For an op amp with simple n-p-n input stage we get the waveform $v_{out}(t)$, which exhibits a step slew "enhancement" on the positive going output, and a slew "degradation" on the negative going output. For a p-n-p input stage, these effects are reversed as shown by $v_{out}(t)$.

Analyze the slowing conditions for the pnp input stage:



Slew "Enhancement"

